NSN 5961-01-024-1010

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view Online at https://aerobasegroup.com/nsn/5961-01-024-1010
Inclosure Material:
Metal
Overall Length:
1.252 inches
Overall Height:
0.340 inches
Overall Width:
0.700 inches
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
400.0 collector to base voltage/static/emitter open and 300.0 collector to emitter voltage/static/base open and 6.0 emitter to base voltage
static, collector open
Current Rating Per Characteristic:
Between 500.00 milliamperes source cutoff current and 2.00 amperes source cutoff current
Power Rating Per Characteristic:
20.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Precious Material And Location:
Terminal surface option gold
Precious Material:
Gold
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Terminal Type And Quantity:
2 uninsulated wire lead and 1 case
Specification Data:
81349-mil-s-19500/454 government specification
Shelf Life:

N/a

Unit Of Measure:

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No

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